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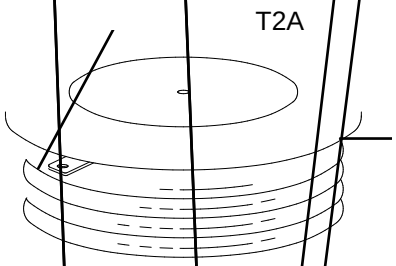


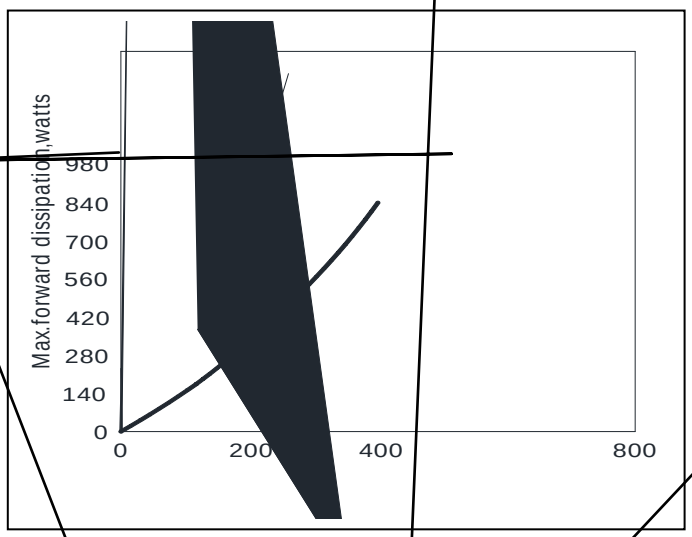
Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP610/12	1200	1200	1400
KP610/14	1400	1400	1600
KP610/16	1600	1600	1760
KP610/18	1800	1800	1900

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	2 mA 25 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/ s

Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		120		mA	V_D =12 V;R_L = 3 ohms;T_j = +25 °C
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_D = 12 V;R_L = 3 ohms;T_j = +25 °C
Peak negative voltage	V_{GRM}		5		V	

Delay time	t_d		3.0	2.5	s	I_{TM}=100A; V_D=67%V


Max.forward dissipation,watts
980
840
700
560
420
280
140
0
0
200
400
800